

19. (Added) The manufacturing process for a silicon epitaxial wafer according to claim 11, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

20. (Added) The manufacturing process for a silicon epitaxial wafer according to claim 12, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony.

21. (Added) The manufacturing process for a silicon epitaxial wafer according to claim 13, wherein a dopant in a substrate of the silicon epitaxial wafer is boron, arsenic or antimony. --

#### REMARKS

The above amendments to the claims have been made to correct the multiple dependency of the claims and to put the application in better condition for examination. No new matter has been added.

[illegible]

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